

N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

Rev. 02 — 12 July 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

Table 1

- DC-to-DC convertors
- Lithium-ion battery protection

Quiek reference dete

Load switching

Improved mechanical and thermal characteristics

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference	data				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	106	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R_{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	5.6	mΩ
	resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; I_D = 15 \; A; \\ T_j = 25 \; ^\circ C; \; see \; \underline{Figure \; 12}; \\ see \; \underline{Figure \; 13} \end{array}$	-	3.2	4.2	mΩ



N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

Table 1.	Quick refer	ence data	continued

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$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Dynamic	characteristics					
$\begin{array}{c} \text{G}(\text{tot}) & \text{total gate charge} & \text{see } \hline \text{Figure 15} & \text{see } \hline \ \text{Figure 15} & \text{see } \hline \ \text{Figure 15} & \text{see } \hline \text{Figure 15} & \text{see } \hline \text{Figure 15} & \text{see } \hline \ \text{Figure 15} & \text{see } \hline \ Figure$	Q _{GD}	gate-drain charge		-	7	-	nC
$ \begin{array}{c} E_{DS(AL)S} & \text{non-repetitive} \\ \text{drain-source} & I_{D} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}C; \\ I_{D} = 100 \; A; \; V_{sup} \leq 40 \; V; \end{array} $	Q _{G(tot)}	total gate charge		-	38	-	nC
drain-source $I_D = 100 \text{ A}; V_{sup} \le 40 \text{ V};$	Avalanch	e ruggedness					
	E _{DS(AL)S}	drain-source	$I_D = 100 \text{ A}; V_{sup} \le 40 \text{ V};$	-	-	77	mJ

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate	Q	
mb	D	drain	ប៉ូប៉ូប៉ូប៉	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

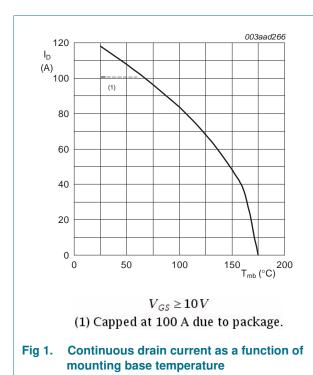
Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
PSMN4R0-40YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

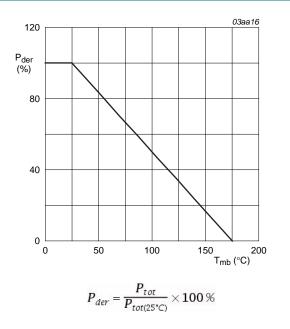
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

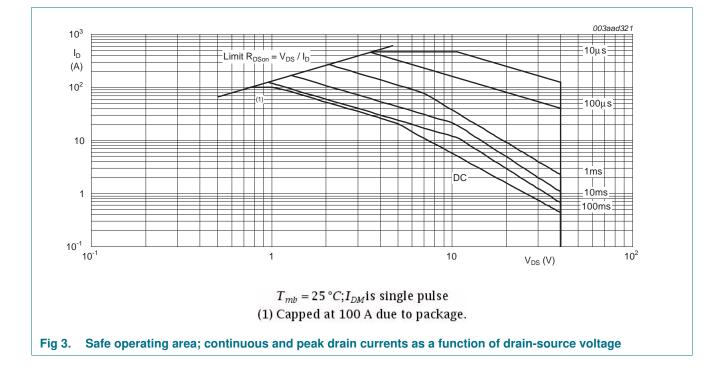
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			5, (
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
$\begin{split} & \text{I}_{D} & \text{drain current} & \begin{array}{c} V_{\text{GS}} = 10 \text{ V}; \text{T}_{\text{mb}} = 100 \ ^{\circ}\text{C}; \text{ see Figure 1} & - & 83 & \text{A} \\ \hline V_{\text{GS}} = 10 \text{ V}; \text{T}_{\text{mb}} = 25 \ ^{\circ}\text{C}; \text{ see Figure 1} & - & 100 & \text{A} \\ \hline I_{\text{DM}} & \text{peak drain current} & \text{pulsed; } t_p \leq 10 \ \mu\text{s}; \text{T}_{\text{mb}} = 25 \ ^{\circ}\text{C}; \text{ see Figure 1} & - & 106 & \text{W} \\ \hline \text{see Figure 3} & & - & 106 & \text{W} \\ \hline \text{T}_{\text{stg}} & \text{storage temperature} & & -55 & 175 & ^{\circ}\text{C} \\ \hline \text{T}_{\text{stg}} & \text{storage temperature} & & -55 & 175 & ^{\circ}\text{C} \\ \hline \text{T}_{\text{sld}(\text{M})} & \text{peak soldering temperature} & & - & 260 & ^{\circ}\text{C} \\ \hline \text{Source-drain diode} & & & & \\ \hline \text{I}_{\text{S}} & \text{source current} & \text{T}_{\text{mb}} = 25 \ ^{\circ}\text{C} & & - & 100 & \text{A} \\ \hline \text{I}_{\text{SM}} & \text{peak source current} & \text{pulsed; } t_p \leq 10 \ \mu\text{s}; \ \ \text{T}_{\text{mb}} = 25 \ ^{\circ}\text{C} & & - & 472 & \text{A} \\ \hline \text{Avalanche ruggedness} & & & \\ \hline \text{E}_{\text{DS}(\text{AL})\text{S}} & \text{non-repetitive drain-source} & V_{\text{GS}} = 10 \ \text{V}; \ \text{T}_{\text{j(init)}} = 25 \ ^{\circ}\text{C}; \ \text{I}_{\text{D}} = 100 \ \text{A}; & - & 77 & \text{m}_{\text{A}} \\ \hline \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & & \\ \hline \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & & \\ \hline \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & & \\ \hline \text{C}_{\text{SM}} & & \\ \hline \text{C}_{\text{SM}} & \text{C}_{\text{SM}} & & \\ \hline \text{C}_{$	V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	40	V
$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see Figure 1}$ -100A I_{DM} peak drain currentpulsed; $t_p \le 10 \mu\text{s}; T_{mb} = 25 \text{ °C};$ -472A P_{tot} total power dissipation $T_{mb} = 25 \text{ °C};$ see Figure 2-106W T_{stg} storage temperature-55175°C T_j junction temperature-55175°C $T_{std}(M)$ peak soldering temperature-260°CSource-drain diodeIssource current $T_{mb} = 25 \text{ °C}$ -100AIssource current $T_{mb} = 25 \text{ °C}$ -100AIssource current $T_{mb} = 25 \text{ °C}$ -100AIssource current $V_{GS} = 10 \mu; T_{mb} = 25 \text{ °C}$ -472AEDS(AL)Snon-repetitive drain-source $V_{GS} = 10 V; T_j(init) = 25 \text{ °C}; I_D = 100 ;$ -77m	V _{GS}	gate-source voltage		-20	20	V
IDMpeak drain currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C;$ -472APtottotal power dissipation $T_{mb} = 25 \ ^{\circ}C;$ see Figure 2-106WTstgstorage temperature-55175^{\circ}CTjjunction temperature-55175^{\circ}CT_sld(M)peak soldering temperature-260^{\circ}CSource-drain diodeIssource current $T_{mb} = 25 \ ^{\circ}C$ -100AIsMpeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -472AAvalanche ruggednessE_DS(AL)Snon-repetitive drain-source $V_{GS} = 10 \ V; T_{j(init)} = 25 \ ^{\circ}C; \ I_D = 100 \ A;$ -77m.	I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	83	А
see Figure 3 P_{tot} total power dissipation $T_{mb} = 25 ^{\circ}C$; see Figure 2-106W T_{stg} storage temperature-55175°C T_{j} junction temperature-55175°C $T_{sld(M)}$ peak soldering temperature-260°CSource-drain diodeIssource currentT_mb = 25 °C-100AIsMpeak source currentpulsed; $t_p \le 10 \ \mu$; $T_{mb} = 25 ^{\circ}$ C-472AAvalanche ruggednessVGS = 10 V; $T_{j(init)} = 25 ^{\circ}$ C; $I_D = 100 \ A$;-77m.			V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	100	А
T_{stg} storage temperature-55175°C T_j junction temperature-55175°C $T_{sld(M)}$ peak soldering temperature-260°CSource-drain diodeIssource current $T_{mb} = 25 \text{ °C}$ -100AIsMpeak source currentpulsed; $t_p \le 10 \text{ µs}; T_{mb} = 25 \text{ °C}$ -472AAvalanche ruggedness $E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 100 \text{ A};$ -77m.	I _{DM}	peak drain current	· • • • • • • • • • • • • • • • • • • •	-	472	A
$\begin{array}{c cccc} T_{j} & junction \ temperature & -55 & 175 & ^{\circ}C \\ \hline T_{sld(M)} & peak \ soldering \ temperature & - & 260 & ^{\circ}C \\ \hline \hline Source-drain \ diode & & & & \\ \hline I_{S} & source \ current & T_{mb} = 25 \ ^{\circ}C & - & 100 & A \\ \hline I_{SM} & peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}C & - & 472 & A \\ \hline \hline Avalanche \ ruggedness & & & \\ \hline E_{DS(AL)S} & non-repetitive \ drain-source & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \ I_{D} = 100 \ A; & - & 77 & m_{A} \\ \hline \end{array}$	P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	106	W
$\begin{array}{c c} T_{sld(M)} & \text{peak soldering temperature} & - & 260 & ^{\circ}\text{C}\\ \hline \textbf{Source-drain diode} & & & & & \\ \hline I_{S} & \text{source current} & T_{mb} = 25 ^{\circ}\text{C} & - & 100 & \text{A}\\ \hline I_{SM} & \text{peak source current} & \text{pulsed; } t_{p} \leq 10 \mu\text{s; } T_{mb} = 25 ^{\circ}\text{C} & - & 472 & \text{A}\\ \hline \textbf{Avalanche ruggedness} & & & & \\ \hline E_{DS(AL)S} & \text{non-repetitive drain-source} & V_{GS} = 10 \text{V; } T_{j(init)} = 25 ^{\circ}\text{C; } I_{D} = 100 \text{A;} & - & 77 & \text{m}_{S} \end{array}$	T _{stg}	storage temperature		-55	175	°C
Source-drain diodeIssource current $T_{mb} = 25 \text{ °C}$ -100AIsMpeak source currentpulsed; $t_p \le 10 \mu\text{s}; T_{mb} = 25 \text{ °C}$ -472AAvalanche ruggednessEDS(AL)Snon-repetitive drain-sourceVGS = 10 V; Tj(init) = 25 °C; ID = 100 A;-77m.	Tj	junction temperature		-55	175	°C
Issource current $T_{mb} = 25 \text{ °C}$ -100AI_{SM}peak source currentpulsed; $t_p \le 10 \mu\text{s}$; $T_{mb} = 25 \text{ °C}$ -472AAvalanche ruggednessVGS = 10 V; $T_{j(init)} = 25 \text{ °C}$; $I_D = 100 \text{ A}$;-77m	T _{sld(M)}	peak soldering temperature		-	260	°C
$\label{eq:lsm} \begin{array}{c c} peak \mbox{ source current} & pulsed; t_p \leq 10 \ \mu s; T_{mb} = 25 \ ^{\circ} C & - & 472 \ \ A \\ \hline \mbox{ Avalanche ruggedness} & & & \\ \hline E_{DS(AL)S} & \mbox{ non-repetitive drain-source} & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ} C; \ I_D = 100 \ \ A; & - & 77 \ \ mbox{ model} \end{array}$	Source-drain	n diode				
Avalanche ruggedness $E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 100 \text{ A};$ -77model	I _S	source current	T _{mb} = 25 °C	-	100	А
$E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 100 \text{ A};$ - 77 m.	I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	472	А
	Avalanche ru	uggedness				
	$E_{DS(AL)S}$	•		-	77	mJ



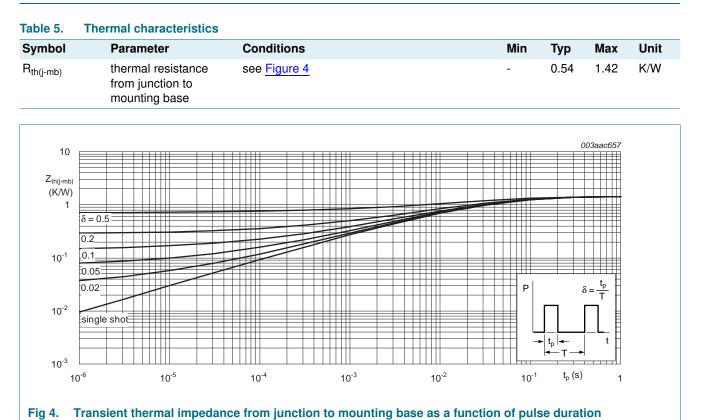




PSMN4R0-40YS



5. Thermal characteristics



6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	36	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10; see Figure 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	3	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 125 °C	-	-	40	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	5.6	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 175 °C; see <u>Figure 12</u>	-	-	8	mΩ
		V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3.2	4.2	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.62	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	31	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	38	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	12	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	7	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; \text{ see } \frac{\text{Figure } 14}{100000000000000000000000000000000000$	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 20 V; V_{GS} = 0 V; f = 1 MHz;$	-	2410	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	504	-	pF
	reverse transfer		-	266	-	pF
C _{rss}	capacitance					
	capacitance turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
C _{rss} t _{d(on)} t _r		$\label{eq:VDS} \begin{split} V_{DS} &= 20 \text{ V}; \text{R}_{\text{L}} = 0.8 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ \text{R}_{\text{G}(\text{ext})} &= 4.7 \Omega \end{split}$	-	18 19	-	ns ns

PSMN4R0-40YS Product data sheet Symbol

Source-drain diode

PSMN4R0-40YS

Тур

Unit

Мах

N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

Min

D	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0$ see <u>Figure 17</u>	$v_{j}, v_{j} = 25 0,$	-	0.83	1.2	V
	reverse recovery time		100 A/µs; V _{GS} = 0 V;	-	42	-	ns
	recovered charge	V _{DS} = 20 V		-	45	-	nC
100 80 60 40 20		003aad154	0	T _j = 150 °C	T _j = 25 °C		
0	1 2	3 _{V_{DS} (V)} 4	0	2 4	6	8 V _{GS} (V)	
0		V _{DS} (V)				•65(•)	
Ū	$T_j = 25 ^{\circ}C$	V _{DS} (V)		$V_{DS} = 25$		•63 (•7	
g 5. Out		n current as a		$V_{DS} = 25$ characteristic of gate-source	5 <i>V</i> s: drain d	current a	
g 5. Out	$T_j = 25 ^{\circ}C$ tput characteristics: drain	n current as a		characteristic	5 <i>V</i> es: drain d e voltage	current a	
1g 5. Out fun 4000 C (pF)	$T_j = 25 ^{\circ}C$ tput characteristics: drain	n current as a tage; typical values	80 g _{rs} (S)	characteristic	5 <i>V</i> es: drain d e voltage	current a ; typical	
g 5. Out fun 4000 C (pF) 3000	$T_j = 25 ^{\circ}C$ tput characteristics: drain	n current as a tage; typical values	80 9 grs 60	characteristic	5 <i>V</i> es: drain d e voltage	current a ; typical	
g 5. Out fun 4000 C (pF) 3000 2000	$T_j = 25 ^{\circ}C$ tput characteristics: drain	n current as a tage; typical values	Solution Solution 91s 0	characteristic	5 <i>V</i> es: drain d e voltage	current a ; typical	valu
g 5. Our fun 4000 C (pF) 3000 2000 1000	$T_j = 25 ^{\circ}C$	003aad159 003aad159 Ciss Ciss Crss Crss VGS (V) 12	function o 80 9/s (S) 60 40 20 0 0 0 2 2 0 0 2 2 2 2 2 2 2 2 2 2 2 2 2	characteristic	5V es: drain o e voltage	current a ; typical	valu

Characteristics ... continued Table 6.

Parameter

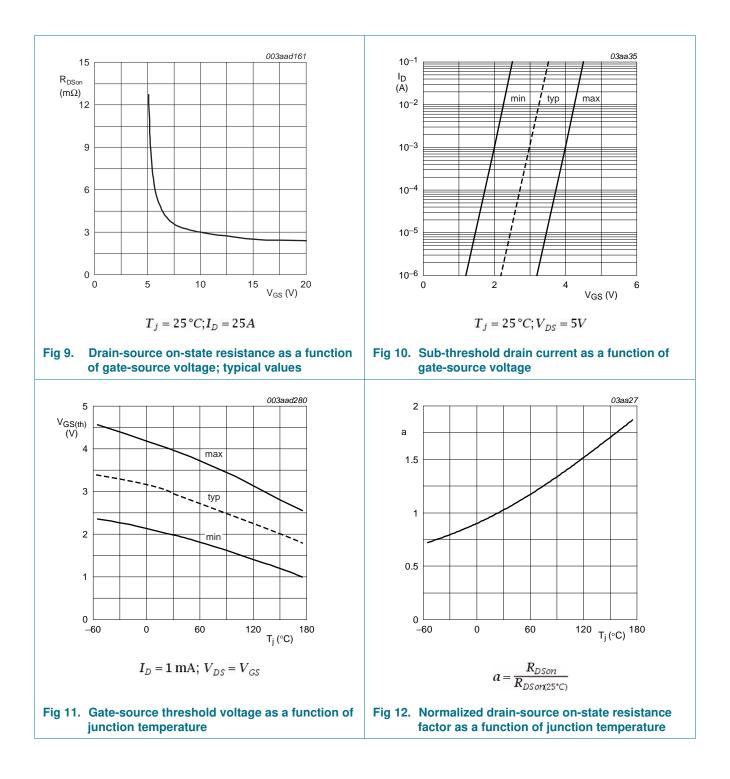
Tested to JEDEC standards where applicable.

Conditions

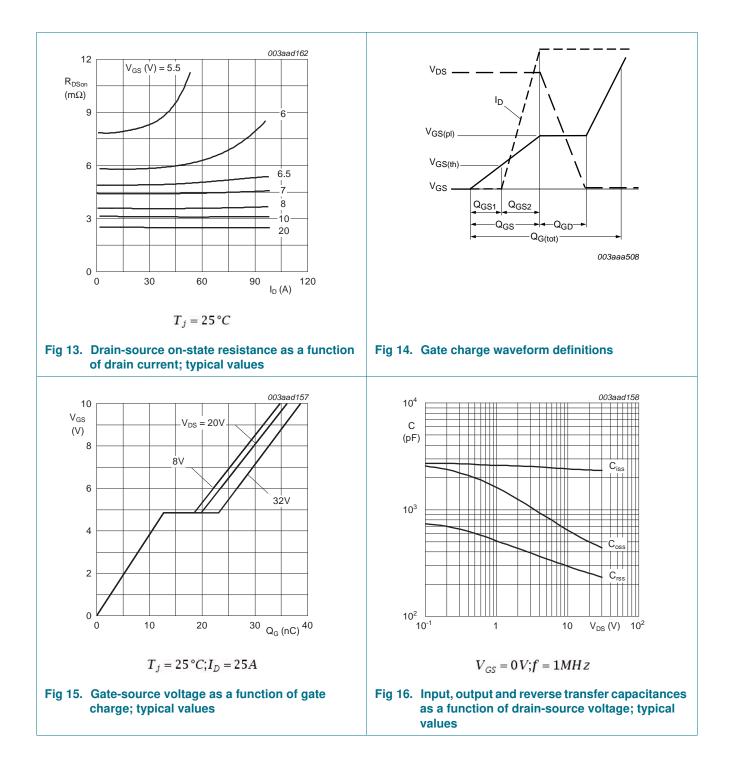
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PSMN4R0-40YS

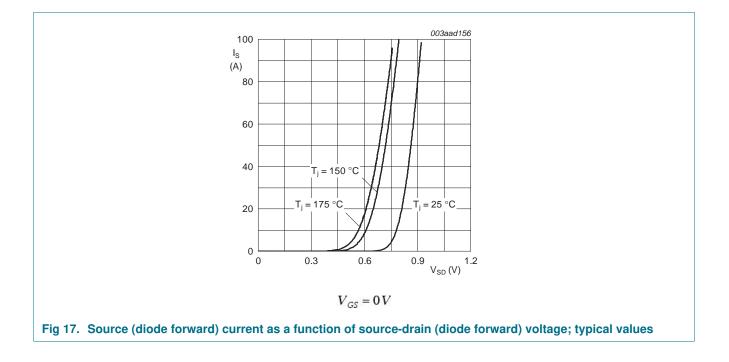
PSMN4R0-40YS



PSMN4R0-40YS



PSMN4R0-40YS



N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

7. Package outline

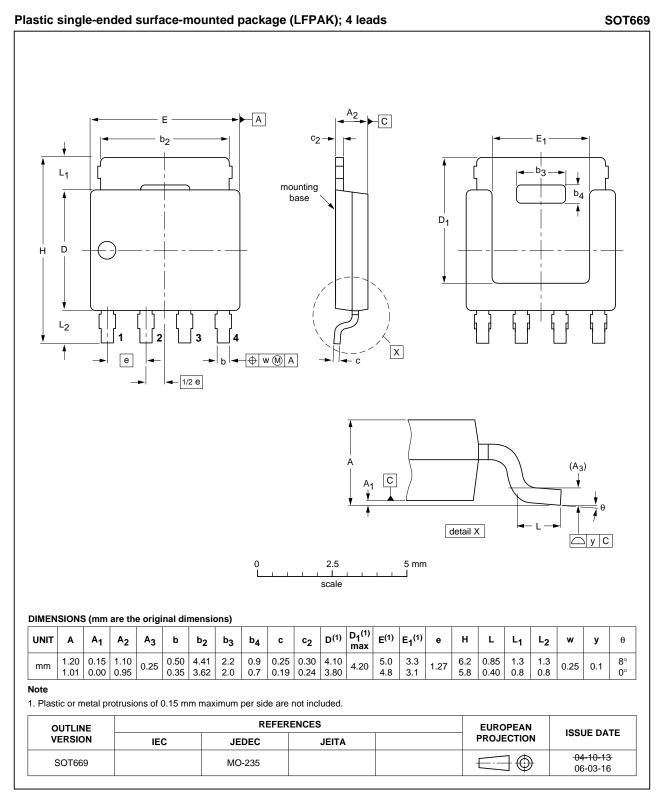


Fig 18. Package outline SOT669 (LFPAK)

information	provided in	n this	document	is	subject	to	legal	disclaim	ers.

PSMN4R0-40YS

All

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R0-40YS v.2	20100712	Product data sheet	-	PSMN4R0-40YS v.1
Modifications:	 Various changes 	to content.		
PSMN4R0-40YS v.1	20090625	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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Product data sheet

N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

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9.4

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10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: <u>salesaddresses@nexperia</u>.com

PSMN4R0-40YS Product data sheet

N-channel LFPAK 40 V 4.2 mΩ standard level MOSFET

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